

January 2014

# FFB2907A / FMB2907A / MMPQ2907A **PNP Multi-Chip General-Purpose Amplifier**

## **Description**

This device is designed for use as a general-purpose amplifier and switch for collector currents to 500 mA. Sourced from Process 63.

### **Block Diagram**



Figure 1. FFB2907A Device Package

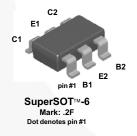


Figure 3. FMB2907A Device Package

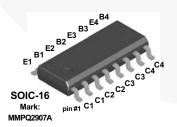


Figure 5. MMPQ2907A Device Package

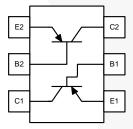


Figure 2. FFB2907A Internal Connections

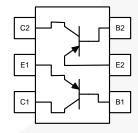


Figure 4. FMB2907A Internal Connections

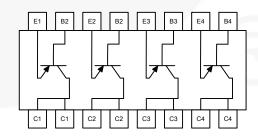


Figure 6. MMPQ2907A Internal Connections

### **Ordering Information**

| Part Number | Top Mark            | Package | Packing Method |
|-------------|---------------------|---------|----------------|
| FFB2907A    | .2F                 | SC70 6L | Tape and Reel  |
| FMB2907A    | .2F                 | SSOT 6L | Tape and Reel  |
| MMPQ2907A   | MMPQ2907A MMPQ2907A |         | Tape and Reel  |

### **Absolute Maximum Ratings**(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25$ °C unless otherwise noted.

| Symbol                            | Parameter                        | Value       | Unit |
|-----------------------------------|----------------------------------|-------------|------|
| V <sub>CEO</sub>                  | Collector-Emitter Voltage        | -60         | V    |
| V <sub>CBO</sub>                  | Collector-Base Voltage           | -60         | V    |
| V <sub>EBO</sub>                  | Emitter-Base Voltage             | -5.0        | V    |
| I <sub>C</sub>                    | Collector Current - Continuous   | -600        | mA   |
| T <sub>J</sub> , T <sub>STG</sub> | Junction and Storage Temperature | -55 to +150 | °C   |

#### Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

#### Thermal Characteristics(3)

Values are at T<sub>A</sub> = 25°C unless otherwise noted.

| Symbol         | Parameter  | Max.     |          |           | Unit  |
|----------------|--|----------|----------|-----------|-------|
| Syllibol       | Faiametei  | FFB2907A | FMB2907A | MMPQ2907A | Oilit |
| D              | Total Device Dissipation                                 |          | 700      | 1,000     | mW    |
| $P_{D}$        | Derate Above 25°C  | 2.4      | 5.6      | 8.0       | mW/°C |
|                | Thermal Resistance, Junction to Ambient                  | 415      | 180      |           |       |
| $R_{	heta JA}$ | Thermal Resistance, Junction to Ambient, Effective 4 Die |          |          | 125       | °C/W  |
|                | Thermal Resistance, Junction to Ambient, Each Die        |          |          | 240       |       |

#### Note:

3. PCB size: FR-4 76 x 114 x 1.57 mm<sup>3</sup> (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

#### Electrical Characteristics(4)

Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

| Symbol                | Parameter  | Conditions  | Min. | Тур. | Max.  | Unit |
|-----------------------|--|---|------|------|-------|------|
| V <sub>(BR)CEO</sub>  | Collector-Emitter Breakdown<br>Voltage <sup>(4)</sup>  | I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0   | -60  |      |       | V    |
| V <sub>(BR)CBO</sub>  | Collector-Base Breakdown Voltage                       | $I_C = -10 \mu\text{A},  I_E = 0$   | -60  |      |       | V    |
| V <sub>(BR)EBO</sub>  | Emitter-Base Breakdown Voltage                         | $I_E = -10  \mu A,  I_C = 0$  | -5.0 |      |       | V    |
| I <sub>BL</sub>       | Base Cut-Off Current                                   | $V_{CE} = -30 \text{ V}, V_{EB} = -0.5 \text{ V}$   |      |      | -50   | nA   |
| I <sub>CEX</sub>      | Collector Cut-Off Current                              | $V_{CE} = -30 \text{ V}, V_{EB} = -0.5 \text{ V}$   |      |      | -50   | nA   |
| I <sub>CBO</sub>      | Collector Cut-Off Current                              | $V_{CB} = -50 \text{ V}, I_{E} = 0$   |      |      | -0.02 | μΑ   |
|                       |  | $V_{CB} = -50 \text{ V}, I_{E} = 0, T_{A} = 125^{\circ}\text{C}$                          |      |      | -20   |      |
|                       |  | I <sub>C</sub> = -0.1 mA, V <sub>CE</sub> = -10 V   | 75   |      |       |      |
| h <sub>FE</sub>       | DC Current Gain  | I <sub>C</sub> = -1.0 mA, V <sub>CE</sub> = -10 V   | 100  |      |       |      |
|                       |  | I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -10 V  | 100  |      |       |      |
|                       |  | $I_C$ = -150 mA, $V_{CE}$ = -10 $V^{(4)}$   | 100  |      | 300   |      |
|                       |  | $I_C$ = -500 mA, $V_{CE}$ = -10 $V^{(4)}$   | 50   |      |       |      |
| M ( 0 )               | Collector-Emitter Saturation<br>Voltage <sup>(4)</sup> | I <sub>C</sub> = -150 mA, I <sub>B</sub> = -15 mA   |      |      | -0.4  | V    |
| V <sub>CE</sub> (sat) |  | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$   |      |      | -1.6  |      |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage                        | $I_C = -150 \text{ mA}, I_B = -15 \text{ mA}^{(4)}$                                       |      |      | -1.3  | V    |
|                       |  | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$   |      |      | -2.6  |      |
| f <sub>T</sub>        | Current Gain-Bandwidth Product                         | I <sub>C</sub> = -50 mA, V <sub>CE</sub> =- 20 V,<br>f = 100 MHz                          |      | 250  |       | MHz  |
| C <sub>ob</sub>       | Output Capacitance                                     | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 100 kHz                                  |      | 6.0  |       | pF   |
| C <sub>ib</sub>       | Input Capacitance                                      | $V_{EB} = -2.0 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$                                 |      | 12   |       | pF   |
| t <sub>on</sub>       | Turn-On Time   |   |      | 30   |       | ns   |
| t <sub>d</sub>        | Delay Time   | $V_{CC} = -30 \text{ V, } I_{C} = -150 \text{ mA,}$<br>$I_{B1} = -15 \text{ mA}$          |      | 8    |       | ns   |
| t <sub>r</sub>        | Rise Time  | 1 10 m/s  |      | 20   |       | ns   |
| t <sub>off</sub>      | Turn-Off Time  |   |      | 80   |       | ns   |
| t <sub>s</sub>        | Storage Time   | $V_{CC} = -6.0 \text{ V}, I_{C} = -150 \text{ mA},$<br>$I_{B1} = I_{B2} = -15 \text{ mA}$ |      | 60   |       | ns   |
| t <sub>f</sub>        | Fall Time  | 181 182 - 10 110 (  |      | 20   | ,     | ns   |

#### Note:

4. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2.0%.

# **Typical Performance Characteristics**

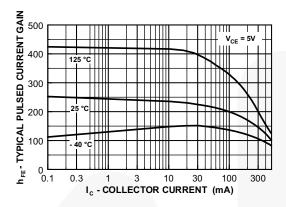


Figure 7. Typical Pulsed Current Gain vs. Collector Current

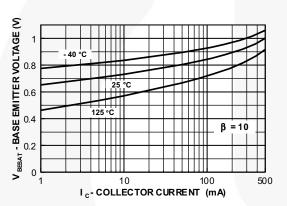


Figure 9. Base-Emitter Saturation Voltage vs. Collector Current

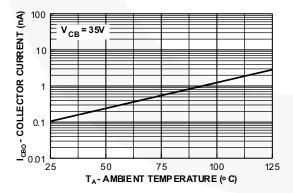


Figure 11. Collector Cut-Off Current vs.
Ambient Temperature

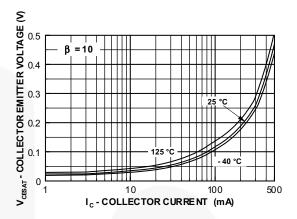


Figure 8. Collector-Emitter Saturation Voltage vs. Collector Current

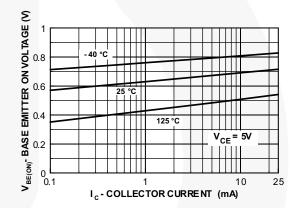


Figure 10. Base-Emitter On Voltage vs. Collector Current

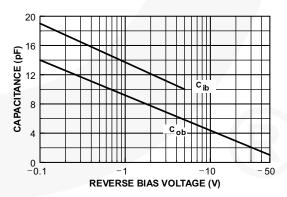


Figure 12. Input and Output Capacitance vs. Reverse Bias Voltage

# **Typical Performance Characteristics** (Continued)

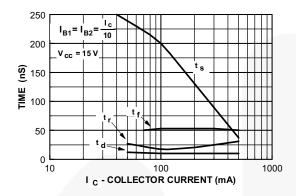


Figure 13. Switching Times vs. Collector Current

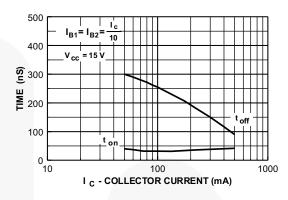


Figure 14. Turn-On and Turn-Off Times vs. Collector Current

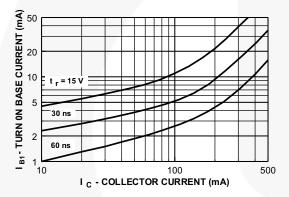


Figure 15. Rise Time vs. Collector and Turn-On Base Current

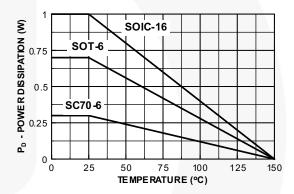
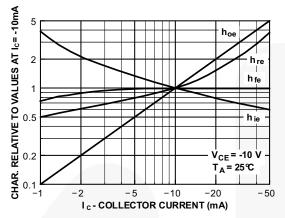


Figure 16. Power Dissipation vs. Ambient Temperature

# **Typical Performance Characteristics** (f = 1.0 kHz)



**Figure 17. Common Emitter Characteristics** 

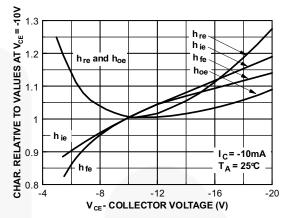


Figure 18. Common Emitter Characteristics

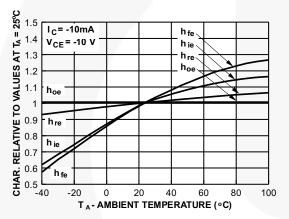


Figure 19. Common Emitter Characteristics

## **Physical Dimensions**

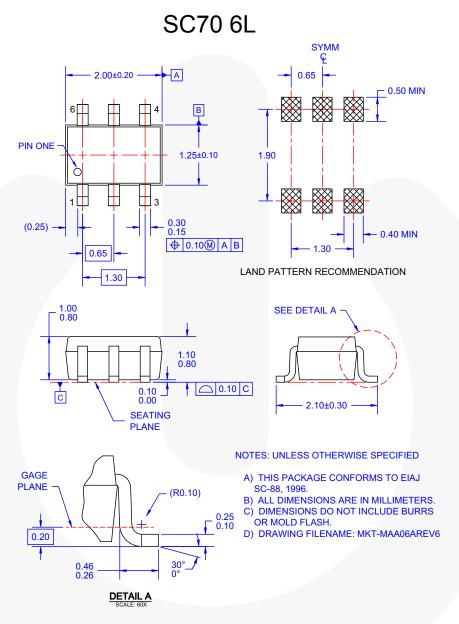


Figure 20. 6-LEAD, SC70, EIAJ SC-88, 1.25 MM WIDE (ACTIVE)

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#### Physical Dimensions (Continued)

# SSOT 6L

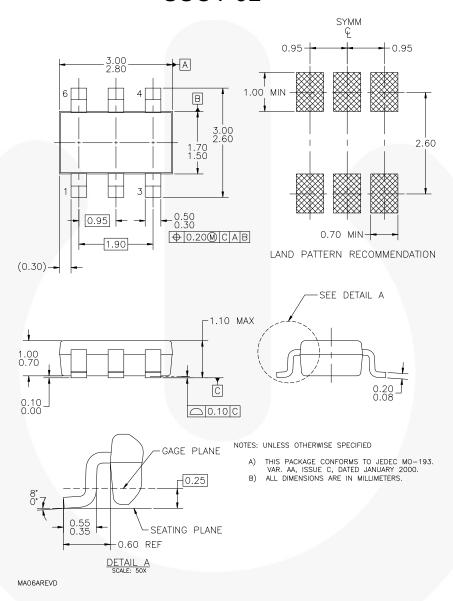


Figure 21. 6-LEAD, SUPERSOT-6, JEDEC MO-193, 1.6 MM WIDE (ACTIVE)

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#### Physical Dimensions (Continued)

# SO 16L NB

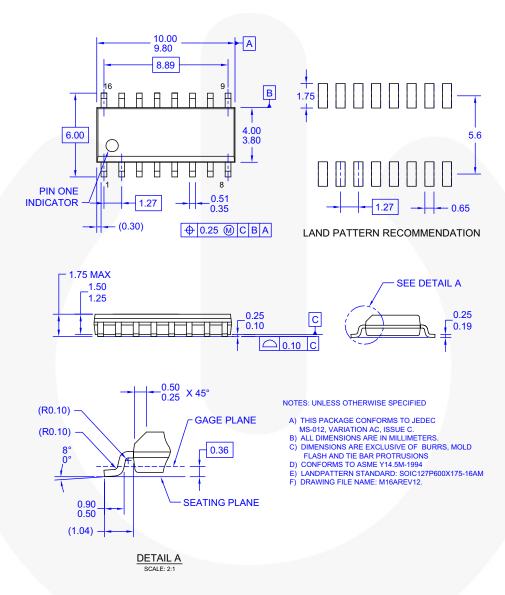


Figure 22. 16-LEAD, SOIC, JEDEC MS-012, 0.150 inch, NARROW BODY (ACTIVE)

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